



University of Pavia

**Ph.D. School in Electronics, Computer Science and Electrical Engineering
Ph.D. School in Microelectronics
National Ph.D School in Micro- and Nano-Electronics**

Resistive read-out and built-in amplification: two key innovations to achieve 4D tracking with silicon sensors

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Abstract: In the past few years, two design innovations have radically changed the performance of silicon detectors and turned silicon sensors into high-resolution timing detectors, fit to meet the very demanding requirements of future 4D trackers. In this presentation, I will review the performance improvements that these two design innovations, low-gain (LGAD) and resistive read-out (RSD), have brought to silicon sensors. Due to the LGAD mechanism, large signals lead to improved temporal precision, while charge sharing, due to the RSD design, has removed the need for very small pixels to achieve excellent spatial precision. LGAD- and RSD-based silicon sensors are now adopted or considered in several future experiments and are the basis for almost every next 4D-trackers.

Organizer

Prof. Lodovico Ratti

Ph.D. Coordinators

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The seminar will take place in English.
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